

**Novel P-dopant for strong and superior surface diamond (Technion)****code:** CHM-1500

This invention presents a new dopant facilitating highly conductive p-type diamond layers (based on transfer doping) that are stable up to at least 350°C. We demonstrated conductance that is over 1 order of magnitude higher than that of diamond surface layers doped by other molecules. Our doping process makes use of standard evaporation deposition which is easy, controllable and tunable. This novel doping makes it an attractive alternative for diamond-based electronic device applications.

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